



Technical Data of Reaction Bonded SiC

Technical Parameter	Unit	SiC
Content of SiC	%	≥88
Density	g/cm ³	≥3.03
Porosity Rate	%	< 0.1
Elastic Modulus	GPa	330 (20°C) 300 (1200°C)
Flexural Strength	MPa	250 (20°C) 280 (1200°C)
Thermal Conductivity	W/mk	45 (1200°C)
	W/mk	110 (20°C)
Thermal expansion	K ⁻¹ × 10 ⁻⁶	4.1
Mohs Hardness	HS	13
Vickers Hardness (load 500g)	Gpa	20
Acid and alkali resistance		Excellent
Compression strength	Gpa	900 (20°C)
Temperature	°C	1380
Weibull modulus		11
Poisson ratio		0.16